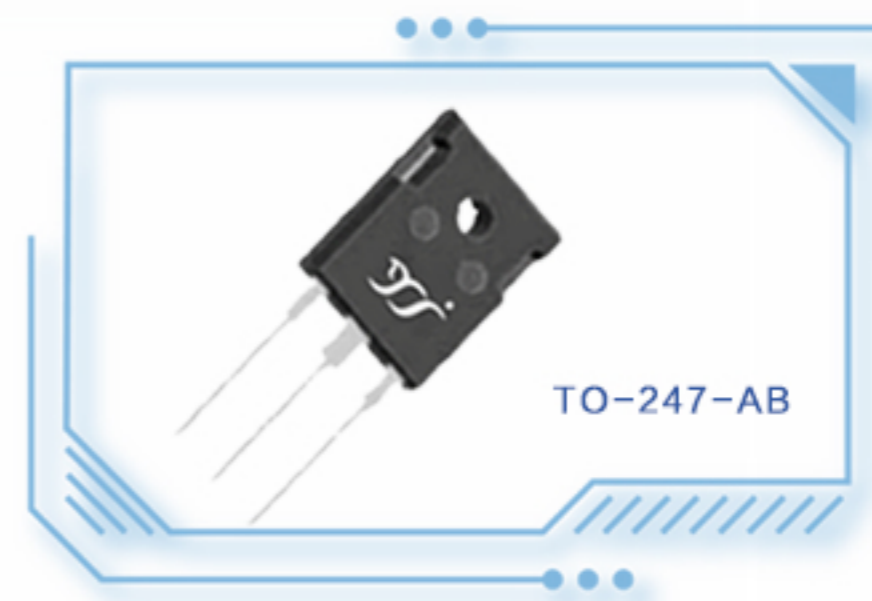
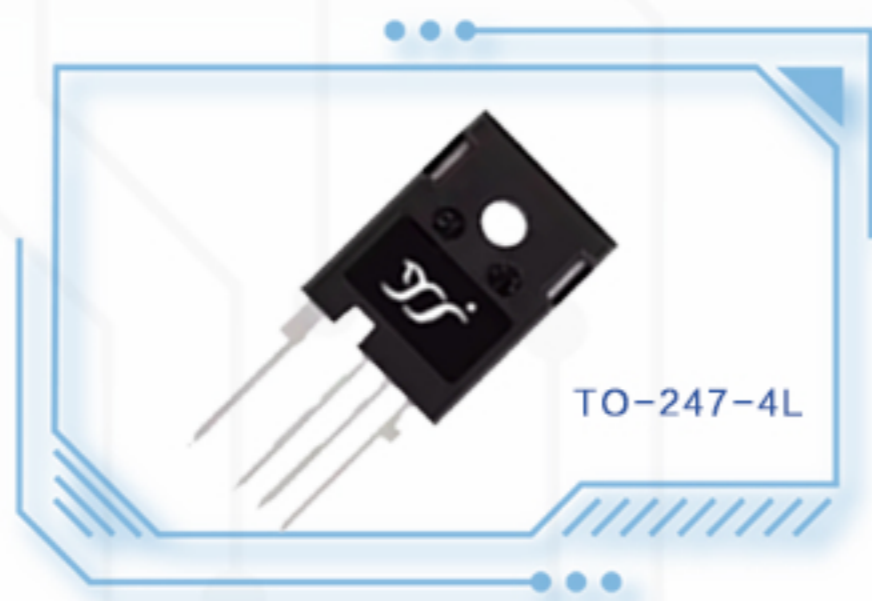


1200V 40mΩ SiC MOSFET

Product Introduction

Since 2021, PV inverter market has entered a period of rapid development, and the demand for SiC power devices has increased rapidly. SiC diodes and Mosfets are used in applications such as BOOST circuits. Due to the high frequency characteristics of the third generation semiconductor materials, the switching frequency of the system can be increased, which can optimize the energy consumption and volume of the entire system. Our SiC Mosfet can match the needs of customers in PV, EV industry, Its switching performance, flow capacity and product reliability can be compared with the best in the industry; It is not only suitable for conventional switch applications, but also meet the control requirements of high voltage and high speed switch applications, using environmental protection materials, in line with RoHS standards



Product Features

High temperature resistance, operating temperature (150°C); Unipolar device, fast switching speed, low loss, suitable for high voltage, high frequency applications;

Using advanced thinning technology, SiC Mosfet has excellent low impedance characteristics and can reduce the energy loss of the device;

TO247AB, TO247-4L and other packaging options;

It has passed the industry's rigorous reliability certification, including high-volume HTRB, HTGB and HV-H3TRB tests;

Electrical Parameters

Product	Blocking Voltage V _{DSS}	Current Rating ID	Generation	R _{dson} (mΩ) at 25°C @V _{GS} =20V	Gate Charge Total Q _g (nC)	Output Capacitance C _{oss} (pF)	Total Power Dissipation P _{TOT} (W)	Thermal resistance R _{thJ-C} (°C/W)	Maximum Junction Temperature (°C)	Package
YJD212040NCFG1	1200V	63A	Gen1	40	120	141	298	0.42	150	TO247-4L
YJD212040NCTG1	1200V	63A	Gen1	40	120	141	298	0.42	150	TO247AB

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Application



PV Inverters



EV Application



Charging Station



Power Supply